

Pressure-induced quantum critical phenomena in YbNiGe_3

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The electrical resistivity of a single crystal YbNiGe_3 has been measured under pressures up to 6.5 GPa and at temperatures down to 0.3K. The resistivity is described as $\rho(T) = \rho_0 + AT^n$ at $T < 20$ K. The coefficient A increases by a factor of 10 with increasing pressure from 3.6 GPa to 6.5 GPa. For $P > 3.6$ GPa, the exponent n decreases below 2, and reaches 1.6 at 6.5 GPa. This value is close to 1.5 expected at the quantum critical point by the spin-fluctuation theory for a three-dimensional antiferromagnet. These findings suggest that the quantum critical point in YbNiGe_3 is located at approximately 8 GPa.

1. Introduction

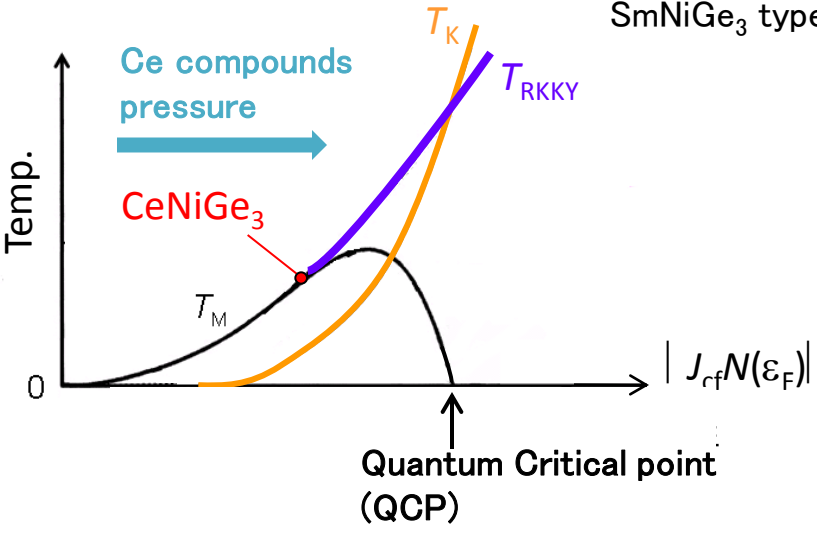
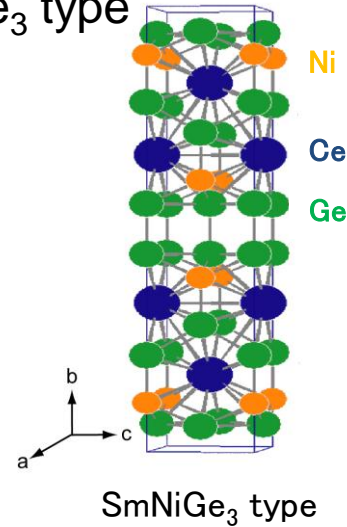
Pressure-induced superconductivity in a heavy-fermion antiferromagnet CeNiGe₃ [1,2]

- CeNiGe₃
Orthorhombic SmNiGe₃ type

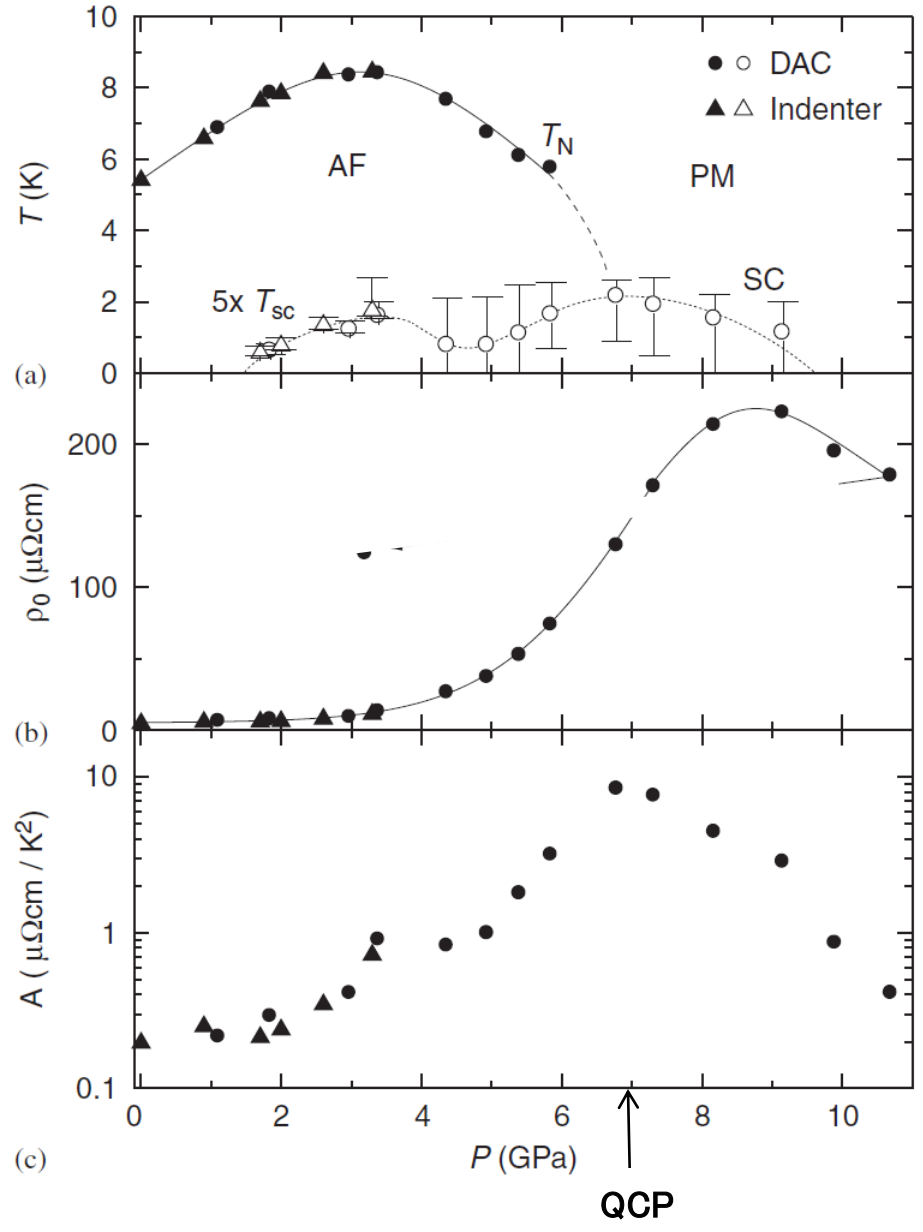
$T_M = 5.5 \text{ K @ } P = 0$

$P_c \sim 6\text{-}7 \text{ GPa [1,2]}$

$T_{SC} \sim 0.4 \text{ K [1,2]}$

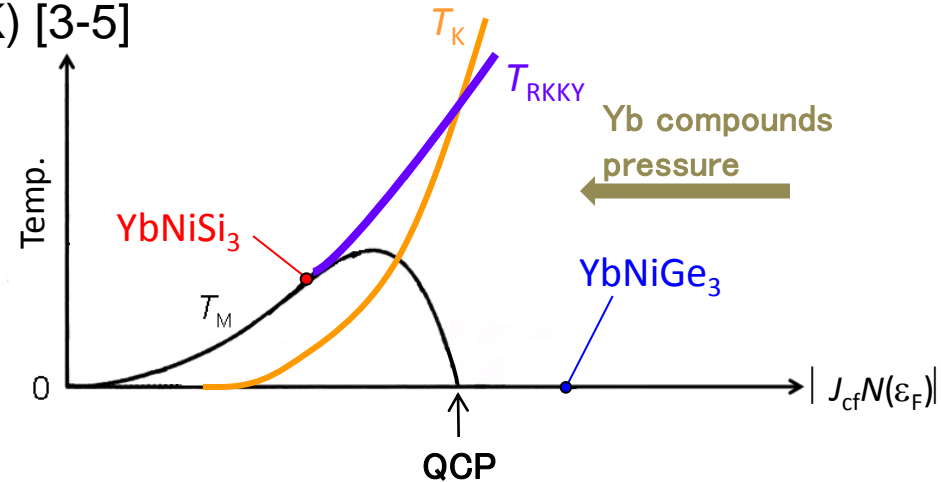


$\rho = \rho_0 + AT^2$
 ρ_0 and A have a maximum around QCP.



Search for a pressure-induced superconductivity in Yb compounds ③

- YbNiSi_3
Orthorhombic SmNiGe_3 type same as CeNiGe_3
Heavy-fermion antiferromagnet ($T_N = 5.1$ K) [3-5]
- YbNiGe_3
Orthorhombic SmNiGe_3 type
Non-magnetic ground state at $P = 0$
Unit cell volume (V_{UC}) is larger by 12% than that for YbNiSi_3 [4,5]



$$V_{\text{UC}}(\text{YbNiGe}_3 @ P = 11 \text{ GPa}) = V_{\text{UC}}(\text{YbNiSi}_3 @ P = 0)$$

(if the bulk modulus is 100 GPa.)

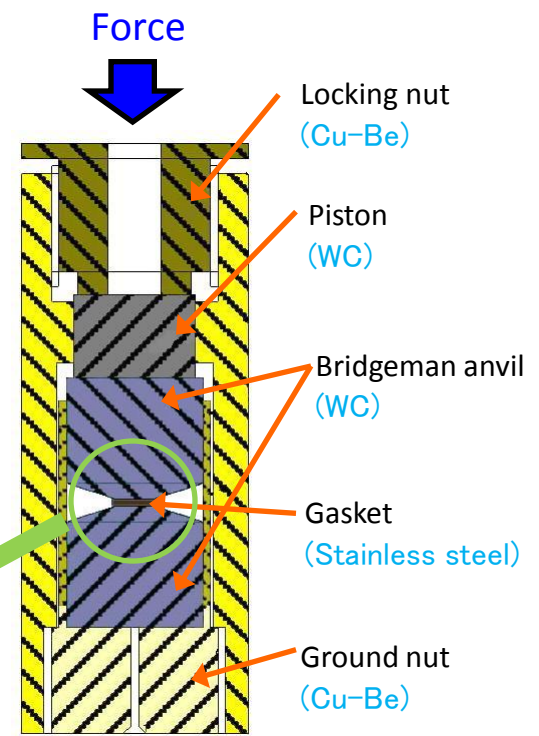
When YbNiGe_3 is pressurized, we expect that the ground state changes to a magnetically ordered state through the QCP.

Purpose : Search for a pressure-induced superconductivity in YbNiGe_3

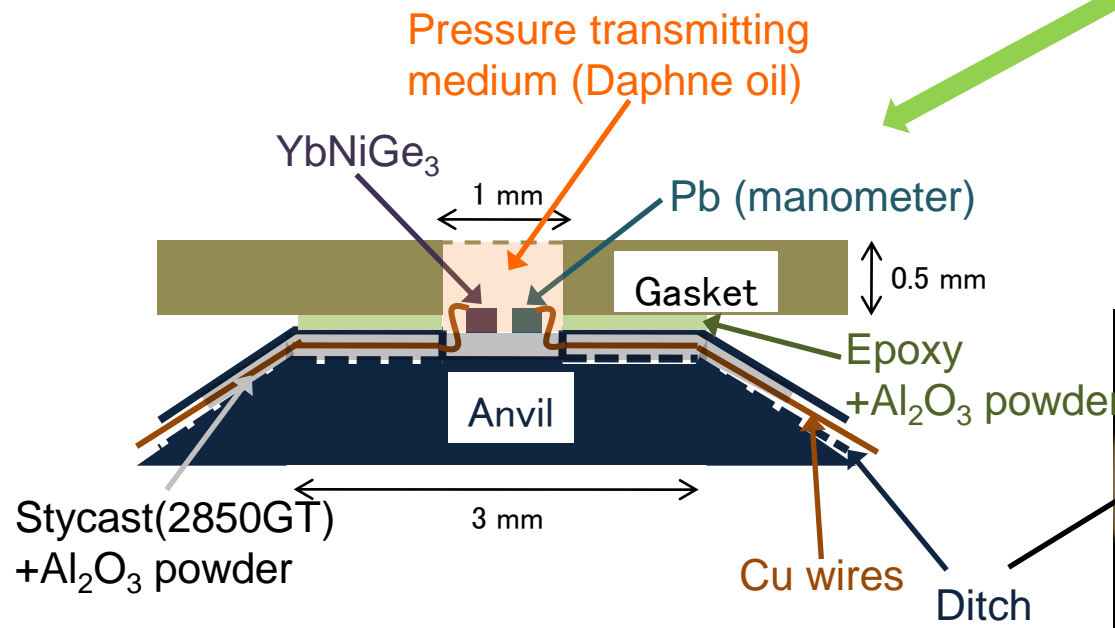
2. Experimental procedure

Electrical resistivity measurement
ac four-terminal method
Clamp type pressure cell
 $T : 0.3 \sim 300 \text{ K}$ (^3He cryostat)

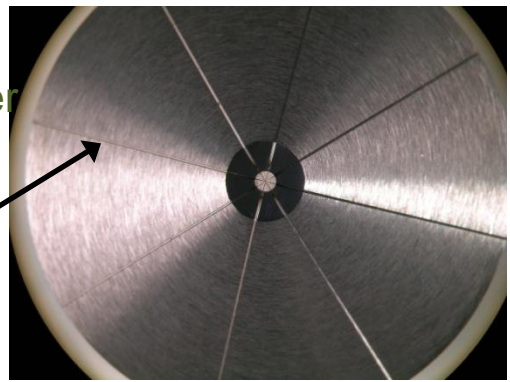
Bridgman anvil cell



Cross section of the sample space [6]



Top view of anvil



Setting of the samples

Top view of anvil

1

3 mm

2

YbNiGe₃

3

Cu wire

Pb

Epoxy+Al₂O₃ powder

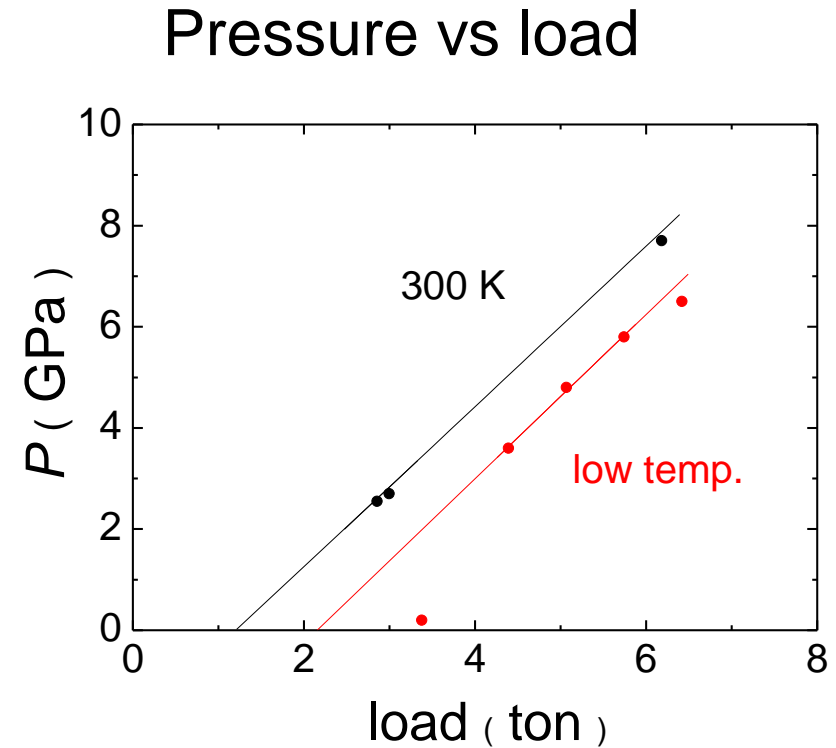
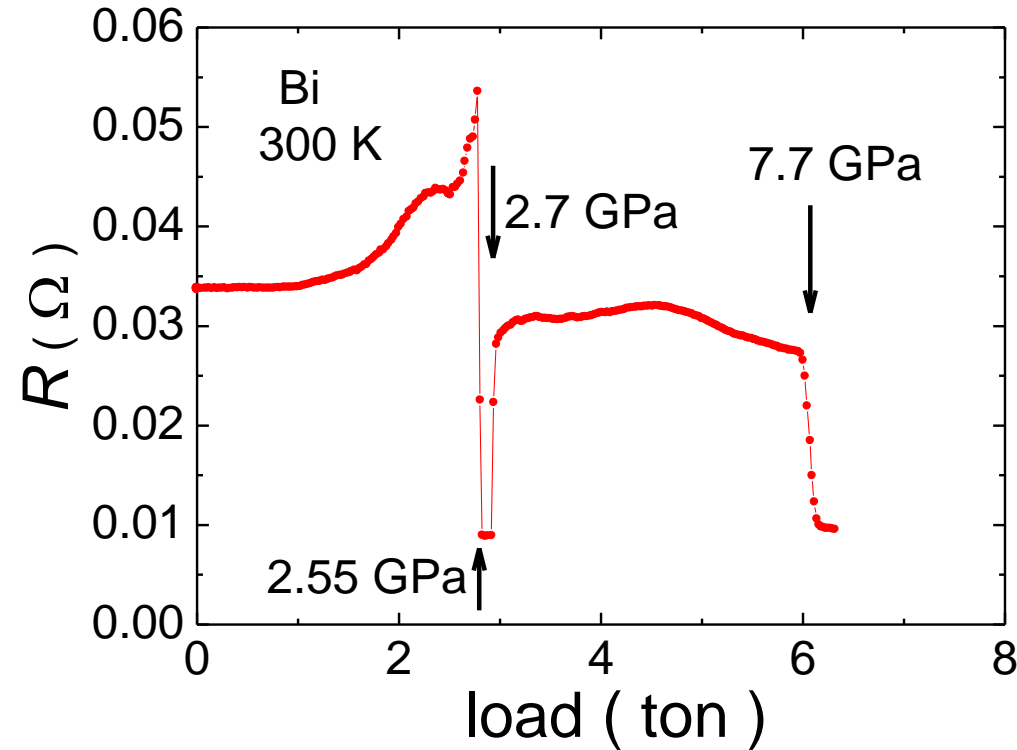
Gasket

0.8 mm

Stycast (2850GT)+Al₂O₃ powder

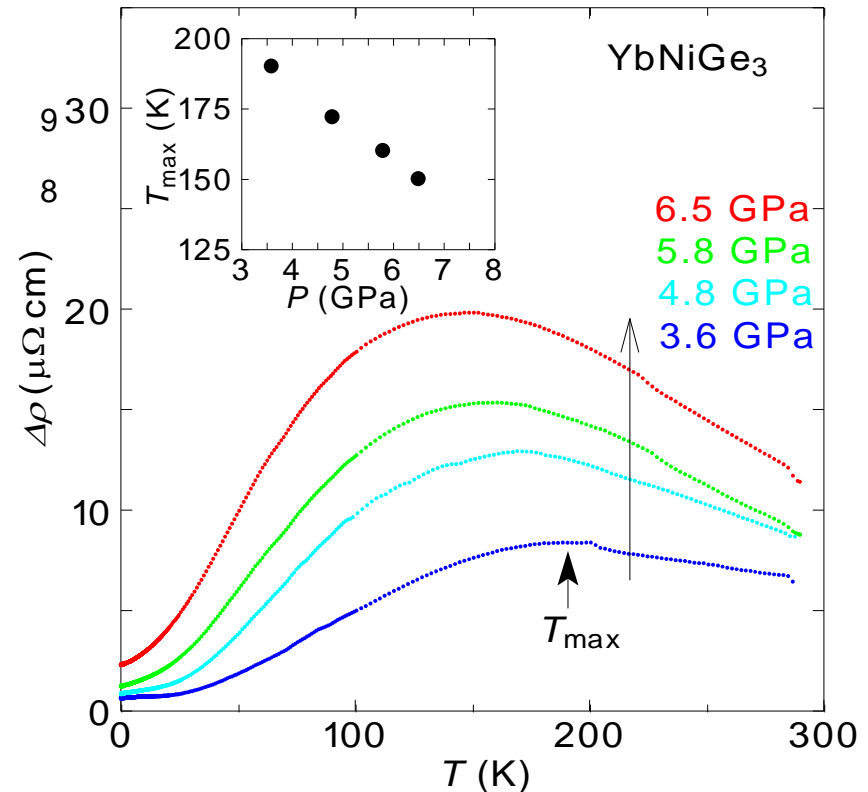
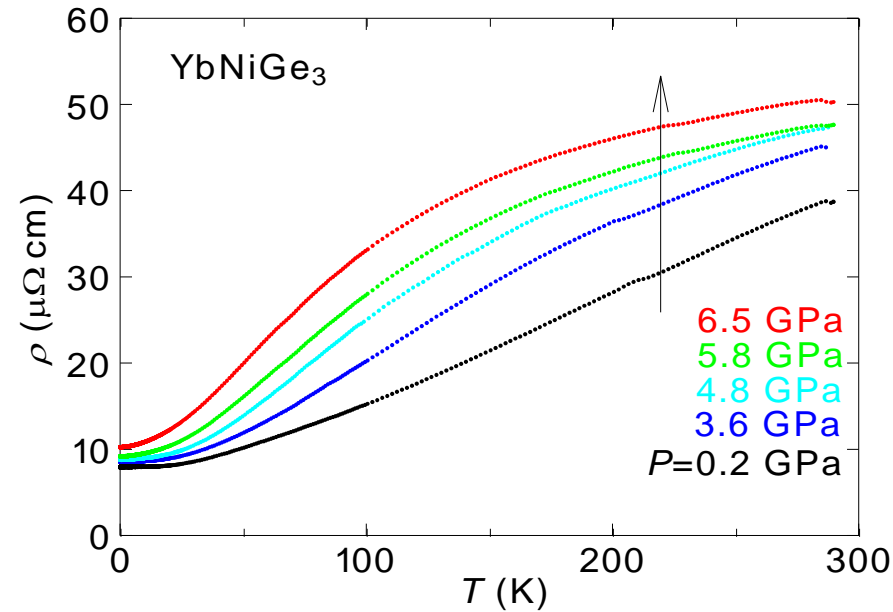
3. Results

Pressure effect on the resistivity of Bi at room temp.



Bi : I - II (2.55 GPa), II - III (2.7 GPa), III - V (7.7 GPa)

Electrical resistivity of YbNiGe₃ under pressures



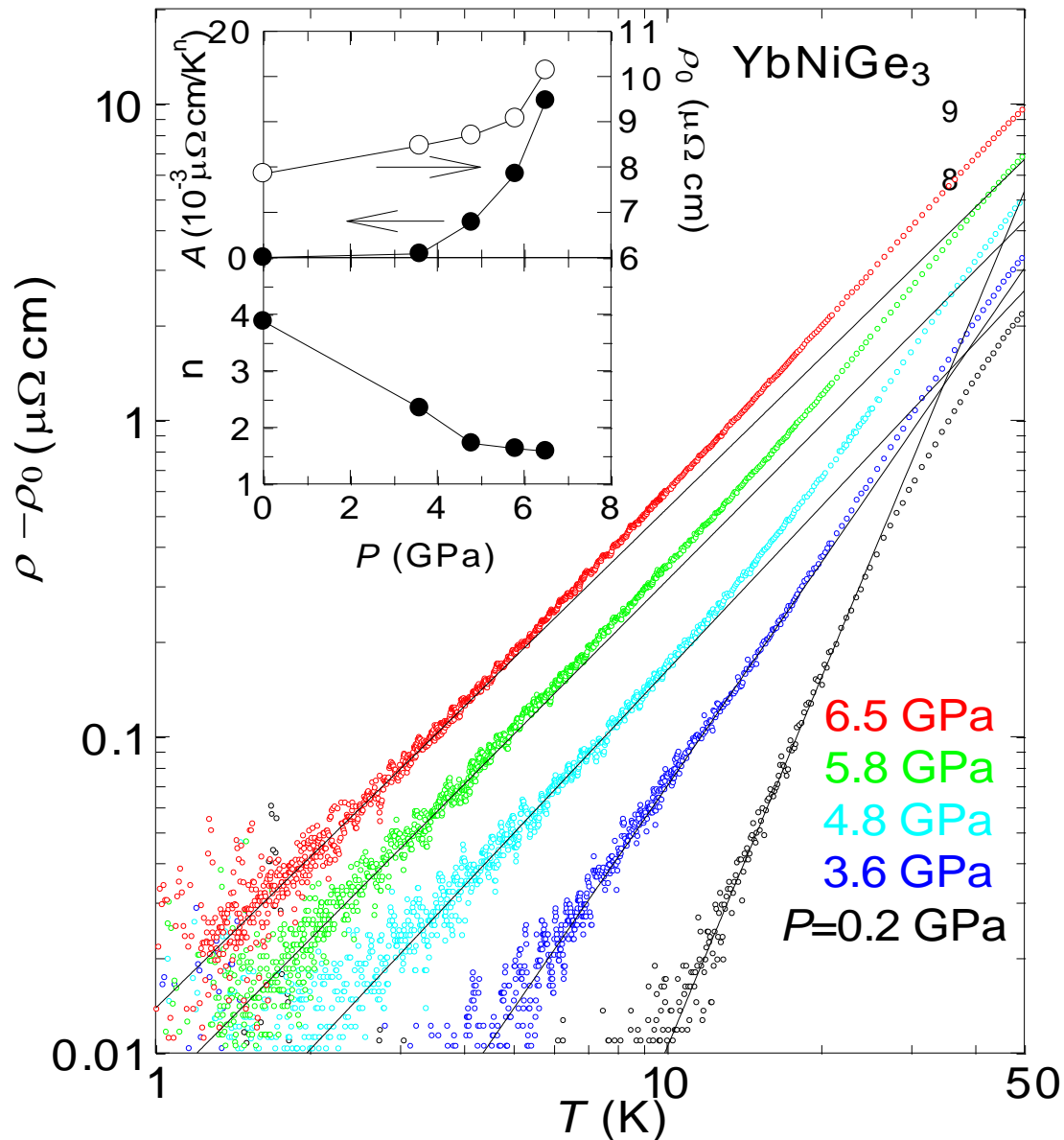
- At $P=0$, $\rho(T)$ behaves such as a normal metal without the Kondo effect.
- With increasing pressure, the resistivity increases and the Kondo effect manifests itself.

- The magnetic contribution $\Delta\rho$

$$\Delta\rho = \rho(P) - \rho(P=0.2 \text{ GPa})$$
- The maximum at T_{\max} is due to the Kondo effect.
- T_{\max} decreases linearly with pressure.
 $\Rightarrow T_K$ decreases with pressure.

Electrical resistivity of YbNiGe₃ at low temperature

⑧

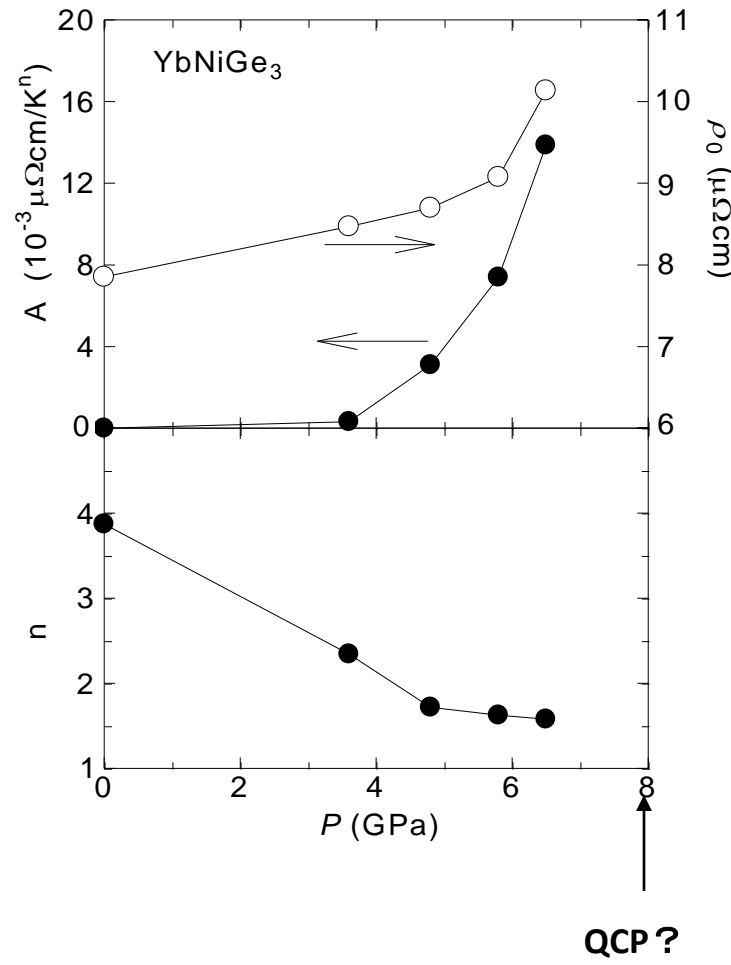


- $\rho(T) = \rho_0 + AT^n$ at $T < 20$ K
- ρ_0 and A increase steeply for $P \geq 4$ GPa.
 \Rightarrow approaching QCP
- The exponent n decrease below 2 for $P \geq 4$ GPa.
- The n reaches 1.6 at 6.5 GPa.
 \Rightarrow spin fluctuation for a three-dimensional antiferromagnet.

4. Summary

Electrical resistivity of YbNiGe₃ under pressures up to 7 GPa.

- T_K increases with pressure.
- The resistivity ρ is described as $\rho(T) = \rho_0 + AT^n$ at $T < 20$ K.
- For $P \geq 4$ GPa, ρ_0 and A increase steeply, and exponent n decreases below 2.
 - ⇒ approaching QCP
- At $P = 6.5$ GPa, n reaches 1.6.
 - ⇒ spin fluctuation for a three-dimensional antiferromagnet.
- QCP is located at about 8 GPa.



References

- [1] M. Nakashima, et al., J. Phys. Condens. Matter. **16** (2004) L255.
- [2] H. Kotegawa, et al., J. Phys. Soc. Jpn., **75** (2006) 044713.
- [3] M. A. Avila, M. Sera, and T. Takabatake, Phys. Rev. B **70** (2004) 100409(R).
- [4] K. Grube, Th. Wolf, C. Meingast and H. v. Löhneysen, Physica B **378-380** (2006) 750.
- [5] Y. Kobayashi, T. Onimaru, M. A. Avila, K. Sasai, M. Soda, K. Hirota, and T. Takabatake, J. Phys. Soc. Jpn., **77** (2008) 124701.
- [6] M. Ohashi and G. Oomi, Special Issue of the Review of High Pressure Science and Technology, **14** (2004) 292.

